								R	EVISI	ONS										
LTR					۵	DESCF	RIPTIC	N					DA	TE (YI	R-MO-	DA)		APPR	OVED)
А	Add char	devic nges t	e types hrough	s 07 th iout.	rough	109. L	Jpdate	boiler	plate.	Editor	ial		95-12-07			M. A. Frye				
В	Add	devic	e type	10. E	ditoria	al chan	ges th	rougho	out.				96-08-09			Raymond Monnin				
С	Boile	erplate	e upda	te, par	t of 5	year re	eview.	ksr					06-08-16				Raymond Monnin		nin	
REV																				
SHEET	6																			
SHEET	15																			
REV STATU	s is			RE\	/ /		С	С	С	С	С	С	С	С	С	С	С	С	С	С
OF SHEETS				SHE	EET		1	2	3	4	5	6	7	8	9	10	11	12	13	14
PMIC N/A				PRE	PARE	ED BY th S. F	Rice			DEFENSE SUPPLY CENTER COLUMBUS										
STANDARD MICROCIRCUIT DRAWING							C	OLUM http	IBUS <u>,</u> b://ww	, OHI(/w.ds	D 432 cc.dla	218-39 a.mil	990							
THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS AND AGENCIES OF THE DEPARTMENT OF DEFENSE			APPROVED BY Michael A. Frye DRAWING APPROVAL DATE 89-02-02				MICROCIRCUIT, MEMORY, DIGITAL, CMOS, 4K X 1 AND 1K X 4 STATIC RANDOM ACCESS MEMORY (SRAM), MONOLITHIC SILICON													
AM	ISC N/A	N		REV	ISION	N LEVI	EL C			SI	ZE A	CA	GE CC 67268	DDE B		59	62-	875	513	
										SHE	ET	·	1	OF	15					

1. SCOPE

1.1 Scope. This drawing describes device requirements for MIL-STD-883 compliant, non-JAN class level B microcircuits in accordance with MIL-PRF-38535, appendix A.

1.2 Part or Identifying Number (PIN). The complete PIN is as shown in the following example:



Voltage on any pin relative to V _{SS} Voltage applied to outputs:	2.0 V dc to +7.0 V dc
devices 01-06, 10	1.0 V dc to V_{CC} + 0.5 V dc
devices 07-09	0.5 V dc to +7.0 V dc
Storage temperature range	65°C to +150°C
Maximum power dissipation (P _D):	
devices 01-06	1.0 W
devices 07-09	0.605 W
device 10	0.660 W
Lead temperature (soldering, 10 seconds)	+260°C
Thermal resistance, junction-to-case (θ_{JC}):	
Case V	See MIL-STD-1835
Case X	15°C/W
Junction temperature (T _J)	+175°C

Generic numbers are listed on the Standard Microcircuit Drawing Source Approval Bulletin at the end of this document and 1/ will also be listed in MIL-HDBK-103.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-87513
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43218-3990		C	2

1.4 Recommended operating conditions.

Supply voltage (V _{CC})	4.5 V dc to 5.5 V dc
Supply voltage (V _{SS})	0 V
Input high voltage (V _{IH})	2.0 V dc to V _{CC} + 0.5 V dc
Input low voltage (V _{IL}):	
devices 01-06, 10	1.0 V dc to 0.8 V dc
devices 07-09	3.0 V dc to 0.8 V dc
Case operating temperature range (T_c)	55°C to +125°C

2. APPLICABLE DOCUMENTS

2.1 <u>Government specification, standards, and handbooks</u>. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATION

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-883 - Test Method Standard Microcircuits. MIL-STD-1835 - Interface Standard Electronic Component Case Outlines.

DEPARTMENT OF DEFENSE HANDBOOKS

MIL-HDBK-103 - List of Standard Microcircuit Drawings. MIL-HDBK-780 - Standard Microcircuit Drawings.

(Copies of these documents are available online at <u>http://assist.daps.dla.mil/quicksearch/</u> or <u>http://assist.daps.dla.mil</u> or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 <u>Item requirements</u>. The individual item requirements shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein. Product built to this drawing that is produced by a Qualified Manufacturer Listing (QML) certified and qualified manufacturer or a manufacturer who has been granted transitional certification to MIL-PRF-38535 may be processed as QML product in accordance with the manufacturers approved program plan and qualifying activity approval in accordance with MIL-PRF-38535. This QML flow as documented in the Quality Management (QM) plan may make modifications to the requirements herein. These modifications shall not affect form, fit, or function of the device. These modifications shall not affect the PIN as described herein. A "Q" or "QML" certification mark in accordance with MIL-PRF-38535 is required to identify when the QML flow option is used.

3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535, appendix A and herein.

3.2.1 <u>Case outlines</u>. The case outlines shall be in accordance with 1.2.2 herein and figure 1.

3.2.2 <u>Terminal connections</u>. The terminal connections shall be as specified on figure 2.

3.2.3 <u>Truth tables</u>. The truth tables shall be as specified on figure 3.

3.3 <u>Electrical performance characteristics</u>. Unless otherwise specified herein, the electrical performance characteristics are as specified in table I and shall apply over the full case operating temperature range.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-87513
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43218-3990		C	3

3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are described in table I.

3.5 <u>Marking</u>. Marking shall be in accordance with MIL-PRF-38535, appendix A. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device.

3.5.1 <u>Certification/compliance mark</u>. A compliance indicator "C" shall be marked on all non-JAN devices built in compliance to MIL-PRF-38535, appendix A. The compliance indicator "C" shall be replaced with a "Q" or "QML" certification mark in accordance with MIL-PRF-38535 to identify when the QML flow option is used.

3.6 <u>Certificate of compliance</u>. A certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6 herein). The certificate of compliance submitted to DSCC-VA prior to listing as an approved source of supply shall affirm that the manufacturer's product meets the requirements of MIL-PRF-38535, appendix A and the requirements herein.

3.7 <u>Certificate of conformance</u>. A certificate of conformance as required in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.

3.8 Notification of change. Notification of change to DSCC-VA shall be required for any change that affects this drawing.

3.9 <u>Verification and review</u>. DSCC, DSCC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

4. VERIFICATION

4.1 <u>Sampling and inspection</u>. Sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.

4.2 <u>Screening</u>. Screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. The following additional criteria shall apply:

- a. Burn-in test, method 1015 of MIL-STD-883.
 - (1) Test condition C or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015 of MIL-STD-883.
 - (2) $T_A = +125^{\circ}C$, minimum.
- b. Interim and final electrical test parameters shall be as specified in table II herein, except interim electrical parameter tests prior to burn-in are optional at the discretion of the manufacturer.

4.3 <u>Quality conformance inspection</u>. Quality conformance inspection shall be in accordance with method 5005 of MIL-STD-883 including groups A, B, C, and D inspections. The following additional criteria shall apply.

- 4.3.1 Group A inspection.
 - a. Tests shall be as specified in table II herein.
 - b. Subgroups 5 and 6 in table I, method 5005 of MIL-STD-883 shall be omitted.
 - c. Subgroup 4 (C_{IN} and C_{OUT} measurement) shall be measured only for the initial test and after process or design changes which may affect capacitance. Sample size is fifteen devices with no failures and all input and output terminals tested.
 - d. Subgroups 7 and 8 shall include verification of the truth table.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-87513
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43218-3990		C	4

	T.	ABLE I. <u>Electrical per</u>	rformance ch	aracter	<u>istics</u> .					
Test	Symbol	Condition	s	Gro	up A	Device		Limits	Unit	
		$-55^{\circ}C \le T_{C} \le +$ $V_{CC} = 4.5 V to$ $V_{SS} = 0 V$ unless otherwise sp	125°C 5.5 V / ecified <u>1</u> /	subg	roups	type	Mir	n Max		
V _{CC} power supply current	I _{CC1}	$t_{AVAV} = t_{AVAV}$ (minimu	um)	1, 2,	3	01-03		80	mA	
(average) <u>Z</u>						04-09		110		
						10		120		
V _{CC} power supply current (standby, stable TTL input levels) 2/	I _{CC2}	$\label{eq:central_constraint} \begin{array}{l} \overline{CE} \ \geq V_{IH}, \ all \ other \ i \\ \leq V_{IL} \ or \geq V_{IH} \end{array}$	inputs	1, 2,	3	01-06, 10		15	mA	
						07-09		10		
V _{CC} power supply current	I _{CC3}	$\overline{\text{CE}} \ \geq (\text{V}_{\text{CC}} \text{ - } 0.2 \text{ V}),$		1, 2,	3	01-06		6.0	mA	
input levels) $\underline{2}$		all other inputs ≤ 0.2 $\geq (V_{CC} - 0.2 \text{ V})$	2 V or			10		10		
V _{CC} power supply current	I _{CC4}	$\overline{\text{CE}} \geq (\text{V}_{\text{CC}} \text{ - } 0.2 \text{ V}),$	all other	1, 2,	3	01-06		10	mA	
input levels) <u>2</u> /		inputs \leq 0.2 V or \geq (V _{CC} - 0.2 V)				10		20		
Input leakage current, any	I_{ILK} $V_{CC} = 5.5 V,$			1, 2,	3	01-06		±5.0	μA	
input		V _{IN} = 0.0 V to 5.5 V				07-10		±10		
Off state output leakage current	I _{OLK}	$V_{CC} = 5.5 V,$ $V_{IN} = 0.0 V \text{ to } 5.5 V$		1, 2,	3	01-06, 10		±10	μΑ	
						07-09		±50	:50	
Output high voltage	V _{OH}	I_{OUT} = -4.0 mA, V_{IH} =	= 2.0 V	1, 2,	3	All	2.4	1	V	
Output low voltage	V _{OL}	$I_{OUT} = 12 \text{ mA}, V_{IL} =$	0.8 V	1, 2,	3	01-03		0.4	V	
		I_{OUT} = 8.0 mA, V_{IL} =	0.8 V	1, 2,	3	04-10		0.4		
Input capacitance	C _{IN}	$V_{IN} = 0.0 \text{ V to } 3.0 \text{ V},$		4		01-06		4.0	pF	
		See 4.3.1c	25 C,			07-10		8.0		
Output capacitance	C _{OUT}	$V_{IN} = 0.0 V \text{ to } 3.0 V,$		4		01-06		4.0	pF	
		$f = 1.0 \text{ MHz}, T_A = +2$ See 4.3.1c	25°C,			07-10		8.0		
Functional tests		See 4.3.1d		7, 8A	, 8B	All				
Chip enable access time	t _{ELQV}	See figures 4 and 5		9, 10	, 11	01,04, 07		25	ns	
					02,05, 08,10		35			
						03,06,09		45		
See footnotes at end of table.										
STAN MICROCIRCI	IDARD JIT DRAV	WING	SIZE A					5962	-87513	
DEFENSE SUPPLY COLUMBUS, C	CENTER C HIO 43218	OLUMBUS -3990			REVISIO	ON LEVEL C		SHEET	5	

Test	Symbol	$\begin{array}{c} \text{Conditions} \\ -55^\circ\text{C} \leq \text{T}_{\text{C}} \leq +12 \\ \text{V}_{\text{CC}} = 4.5 \text{ V to 5} \\ \text{V}_{\text{SS}} = 0 \text{ V} \\ \text{unless otherwise spe} \end{array}$	25°C 5.5 V cified <u>1/</u>	Group A subgroups	Device type	Lin Min	nits Max	Unit			
Read cycle time	t _{AVAV}	See figures 4 and 5	<u>3/</u>	9, 10, 11	01,04, 07	25		ns			
					02,05, 08,10	35					
					03,06, 09	45					
Address access time	t _{AVQV}	See figures 4 and 5	<u>4/</u>	9, 10, 11	01,04, 07		25	ns			
				02,05, 08,10		35					
					03,06, 09		45				
Output hold after address change	hold after address t _{AVQX} See figures 4 and 5 9, 10, 11		9, 10, 11	01-06, 09	5.0		ns				
				10	3.0		-				
					07,08	0					
Chip enable to output	t _{ELQX}	See figures 4 and 5	<u>5</u> /	9, 10, 11	01-06	5.0		ns			
active					07	8		4			
								08,09	10		
					10	2.0					
Chip disable to output inactive	t _{EHQZ}	See figures 4 and 5	<u>5/ 6</u> /	9, 10, 11	01,05, 06, 08- 10	0	20	ns			
					02,03	0	30				
					04,07	0	15				
Chip enable to power up	t _{ELPU}	See figures 4 and 5	<u>5</u> /	9, 10, 11	All	0		ns			
Chip enable to power down	t _{EHPD}	See figures 4 and 5	5/	9, 10, 11	All		30	ns			
Input rise and fall times	t _T	<u>5/ 7</u> /		9, 10, 11	01-09		50	ns			
					10		10				
See footnotes at end of table.											
STAN	IDARD UIT DRAV	WING	SIZE A				5962	2-87513			

DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43218-3990

REVISION LEVEL C	SHEET 6

	TABLE	I. Electrical performa	nce characte	ristics	<u>s</u> - continu	ued.			
Test	Symbol	Condition	s	G	roup A	Device	Li	mits	Unit
		$\begin{array}{c} -55^{\circ}C \leq T_{C} \leq + \cdot \\ V_{CC} = 4.5 \text{ V to} \\ V_{SS} = 0 \text{ V} \\ \text{unless otherwise sp} \end{array}$	125°C 5.5 V / ecified <u>1</u> /	sut	ogroups	type	Min	Мах	
Write cycle time	t _{AVAV}	See figures 4 and 6		9, 1	10, 11	01,04, 07	25		ns
						02,05, 08,10	35		
						03,06, 09	45		
Write pulse width	t _{wLWH}	See figures 4 and 6		9, 1	10, 11	01,04	15		ns
						02,07	20		
						03,05, 10	25		
					08	30			
						06,09	35		
Chip enable to end of write	t _{ELEH}	See figures 4 and 6		9, 10, 11	10, 11	01,04, 07	20		ns
				02,05, 08,10	30				
						03,06, 09	40		
Data setup to end of write	t _{DVWH}	See figures 4 and 6		9, 10, 11		01,05, 06,10	15		ns
						02,03, 08,09	20		
						04	10		
						07	12		
Data hold after end of write	t _{WHDX}	See figures 4 and 6		9, ²	10, 11	All	0		ns
Address setup to end of write	t _{AVWH}	See figures 4 and 6		9, 1	10, 11	01,04, 07	20		ns
						02,05, 08,10	30		
						09	35		
						03,06	40		
See footnotes at end of table.									
STAN MICROCIRCI	IDARD UIT DRAV	WING	SIZE A					5962	8-87513
DEFENSE SUPPLY COLUMBUS, C	CENTER C HIO 43218	OLUMBUS -3990			REVISIO	N LEVEL C		SHEET	7

	TABLE I. Electrical performance characteristics - continued.								
Test	Symbol	ymbol Conditions		Device	Lin	Unit			
		$-55^{\circ}C \le I_{C} \le +125^{\circ}C$ $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$ $V_{SS} = 0 \text{ V}$ unless otherwise specified <u>1</u> /	subgroups	туре	Min	Max			
Address setup to beginning of write	t _{AVWL}	See figures 4 and 6	9, 10, 11	All	0		ns		
Address hold after end of write	t _{WHAV}	See figures 4 and 6	9, 10, 11	All	0		ns		
Write enable to output	t _{WLQZ}	See figures 4 and 6	9, 10, 11	01,04	0	15	ns		
disable				02,03, 05,06, 10	0	20			
				07-09	0	8			
Output active after end of write	t _{WHQX}	See figures 4 and 6 5/8/	9, 10, 11	All	0		ns		

1/ AC measurements assume signal transition times of 5 ns or less, timing reference levels of 1.5 V, input pulse levels of 0.0 V to 3.0 V and output loading of 30 pF load capacitance. Output timing reference is 1.5 V.

2/ I_{CC} is dependent upon output loading and cycle rate. The specified values apply with output(s) unloaded.

- $\underline{3}$ / For read cycles 1 and 2, $\overline{\text{WE}}$ is high for entire cycle.
- $\underline{4}$ Device is continuously selected, \overline{CE} low.
- 5/ Parameter may not be tested, but shall be guaranteed to the limits specified in table I.
- 6/ This parameter is measured ±200 mV from steady state output voltage for device types 01 through 06. For device types 07 through 10, this is measured ±500 mV from steady state output voltage. Load capacitance is 5.0 pF.
- 7/ Measured between VIL maximum and VIH minimum.
- <u>8</u>/ If $\overline{\text{WE}}$ is low when $\overline{\text{CE}}$ goes low, the output remains in the high impedance state.

4.3.2 Groups C and D inspections.

a. End-point electrical parameters shall be as specified in table II herein.

b. Steady-state life test conditions, method 1005 of MIL-STD-883.

- (1) Test condition C or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in method 1015 of MIL-STD-883.
- (2) $T_A = +125^{\circ}C$, minimum.
- (3) Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-87513
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43218-3990		C	8

Case X





Symbol	Millimeters		Inches	
	Min	Max	Min	Max
А	2.08	2.54	.082	.100
b	0.38	0.48	.015	.019
С	0.10	0.18	.004	.007
D	10.72	11.23	.422	.442
E	7.67	8.08	.302	.318
E1	22.3	5 REF	.880 REF	
E2	5.67	5.99	.224	.236
е	1.19 REF	1.35 REF	.047 REF	.053 REF
k	0.20	Nom.	.008	Nom.
k1	0.25 Nom.		.010	Nom.
L	6.86	7.62	.270	.300
Q	0.66		.026	
S2	0.64 Nom		.025	Nom

FIGURE 1. Case outline.

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43218-3990	SIZE A		5962-87513
DEFENSE SUPPLY CENTER COLUMBUS		REVISION LEVEL	SHEET
COLUMBUS, OHIO 43218-3990		C	9

Device types	01-03	04-10
Case outlines	Χ, Υ	Χ, Υ
Terminal number	Terminal	symbol
1	A ₀	A ₆
2	A ₂	A_5
3	A ₆	A ₄
4	A ₈	A ₃
5	A ₁₀	A ₀
6	A ₅	A ₁
7	Q	A ₂
8	WE	CE
9	V_{SS}	V_{SS}
10	CE	WE
11	D	I/O ₄
12	A ₇	I/O ₃
13	A ₁₁	I/O ₂
14	A ₉	I/O ₁
15	A ₄	A ₉
16	A ₃	A ₈
17	A ₁	A ₇
18	V _{cc}	V _{cc}

FIGURE 2. Terminal connections.

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43218-3990	SIZE A		5962-87513
		REVISION LEVEL C	SHEET 10

Device ty	/pes 01	through 03	

CE	WE	Mode	Output	Power
н	х	Not selected	High Z	Standby
L	L	Write	High Z	Active
L	Н	Read	D _{OUT}	Active

H = Logic "1" state L = Logic "0" state X = Don't care

Device types 04 through 10

CE	WE	Mode	Output	Power
н	х	Not selected	High Z	Standby
L	L	Write	D _{IN}	Active
L	н	Read	D _{OUT}	Active

H = Logic "1" state L = Logic "0" state X = Don't care

FIGURE 3. Truth tables.

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43218-3990	SIZE A		5962-87513
		REVISION LEVEL C	SHEET 11











TABLE II. Electrical test requirements.

MIL-STD-883 test requirements	Subgroups (per method 5005, table I)
Interim electrical parameters (method 5004)	
Final electrical test parameters (method 5004)	1*, 2, 3, 7*, 8A, 8B, 9, 10, 11
Group A test requirements (method 5005)	1,2,3,4**,7*,8A,8B, 9,10,11
Groups C and D end-point electrical parameters (method 5005)	1,2, 3

* PDA applies to subgroups 1 and 7.

** See 4.3.1c.

5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-PRF-38535, appendix A.

6. NOTES

6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.

6.2 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractorprepared specification or drawing.

6.3 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished using DD Form 1692, Engineering Change Proposal.

6.4 <u>Record of users</u>. Military and industrial users shall inform Defense Supply Center Columbus (DSCC) when a system application requires configuration control and the applicable SMD. DSCC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronics devices (FSC 5962) should contact DSCC-VA, telephone (614) 692-0544.

6.5 <u>Comments</u>. Comments on this drawing should be directed to DSCC-VA, Columbus, Ohio 43218-3990, or telephone (614) 692-0547.

6.6 <u>Approved sources of supply</u>. Approved sources of supply are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DSCC-VA.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-87513
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 43218-3990		REVISION LEVEL C	SHEET 15

STANDARD MICROCIRCUIT DRAWING BULLETIN

DATE: 06-08-16

Approved sources of supply for SMD 5962-87513 are listed below for immediate acquisition information only and shall be added to MIL-HDBK-103 and QML-38535 during the next revision. MIL-HDBK-103 and QML-38535 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DSCC-VA. This information bulletin is superseded by the next dated revision of MIL-HDBK-103 and QML-38535. DSCC maintains an online database of all current sources of supply at http://www.dscc.dla.mil/Programs/Smcr/.

Standard microcircuit drawing PIN <u>1</u> /	Vendor CAGE number	Vendor similar PIN <u>2</u> /
5962-8751301VA	<u>3</u> /	IMS1203S-25M
5962-8751301XA	<u>3</u> /	IMS1203Y-25M
5962-8751302VA	<u>3</u> /	IMS1203S-35M
5962-8751302XA	<u>3</u> /	IMS1203Y-35M
5962-8751303VA	<u>3</u> /	IMS1203S-45M
5962-8751303XA	<u>3</u> /	IMS1203Y-45M
5962-8751304VA	<u>3</u> /	IMS1223S-25M
5962-8751304XA	<u>3</u> /	IMS1223Y-25M
5962-8751305VA	<u>3</u> /	IMS1223S-35M
5962-8751305XA	<u>3</u> /	IMS1223Y-35M
5962-8751306VA	<u>3</u> /	IMS1223S-45M
5962-8751306XA	<u>3</u> /	IMS1223Y-45M
5962-8751307VA	0C7V7 3DTT2	CY7C148-25DMB P4C148-25CMB
5962-8751308VA	0C7V7 3DTT2	CY7C148-35DMB P4C148-35CMB
5962-8751309VA	0C7V7 3DTT2	CY7C148-45DMB P4C148-45CMB
5962-8751310VA	3DTT2	P4C148-35DMB

- 1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed, contact the Vendor to determine its availability.
- 2/ Caution: Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.
- <u>3/</u> Not available from an approved source.

STANDARD MICROCIRCUIT DRAWING BULLETIN - Continued.

Vendor CAGE <u>number</u>

0C7V7

Vendor name and address

QP Semiconductor 2945 Oakmead Village Court Santa Clara, CA 95051

3DTT2

Pyramid Semiconductor Corporation 1340 Bordeaux Drive Sunnyvale, CA 94089

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Page 2 of 2

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5962-8855206XA CY6116A-35DMB CY7C128A-45DMB CY7C1461KV33-133AXI CY7C199-45LMB GS8161Z36DD-200I GS88237CB-200I R1QDA7236ABB-20IB0 RMLV0408EGSB-4S2#AA0 IS64WV3216BLL-15CTLA3 IS66WVE4M16ECLL-70BLI PCF8570P K6T4008C1B-GB70 CY7C1353S-100AXC AS6C8016-55BIN AS7C164A-15PCN 515712X IS62WV51216EBLL-45BLI IS63WV1288DBLL-10HLI IS66WVE2M16ECLL-70BLI 47L16-E/SN IS66WVE4M16EALL-70BLI IS62WV6416DBLL-45BLI IS61WV102416DBLL-10TLI CY7C1381KV33-100AXC CY7C1381KV33-100BZXI CY7C1373KV33-100AXC CY7C1381KVE33-133AXI CY7C4042KV13-933FCXC 8602501XA 5962-3829425MUA 5962-8855206YA 5962-8866201XA 5962-8866201YA 5962-8866204TA 5962-8866206MA 5962-8866207NA 5962-8866208UA 5962-8872502XA 5962-8959836MZA 5962-8959841MZA 5962-9062007MXA 5962-9161705MXA N08L63W2AB7I 7130LA100PDG GS81284Z36B-250I M38510/28902BVA 5962-8971203XA 5962-8971202ZA 5962-8872501LA